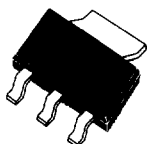


CZTA44**NPN SILICON EXTREMELY
HIGH VOLTAGE TRANSISTOR****SOT-223 CASE****Central™**
Semiconductor Corp.**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CZTA44 type is a surface mount epoxy molded silicon planar epitaxial transistors designed for extremely high voltage applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Collector Current
 Power Dissipation
 Operating and Storage
 Junction Temperature
 Thermal Resistance

SYMBOL

V_{CB0} 450
 V_{CEO} 400
 V_{EBO} 6.0
 I_C 300
 P_D 2.0

UNITS

V
 V
 V
 mA
 W

T_J, T_{stg}
 Θ_{JA}

-65 to +150
 62.5

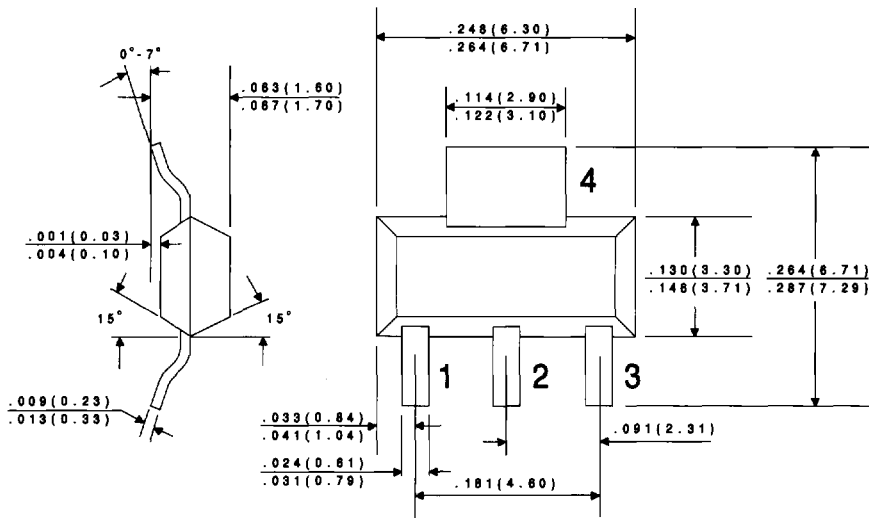
$^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=400\text{V}$		100	nA
I_{CES}	$V_{CE}=400\text{V}$		500	nA
I_{EBO}	$V_{BE}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	450		V
BV_{CES}	$I_C=100\mu\text{A}$	450		V
BV_{CEO}	$I_C=1.0\text{mA}$	400		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=0.1\text{mA}$		0.40	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.50	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.75	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.75	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	40		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	50	200	
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	45		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=10V, I_C=100mA$	20		
f_T	$V_{CE}=10V, I_C=10mA, f=10MHz$	20		MHz
C_{ob}	$V_{CB}=20V, I_E=0, f=1.0MHz$		7.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		130	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DATA SHEET

R2